# Power MOSFET –100V, 275mΩ, –11A, Single P-Channel

This P-Channel Power MOSFET is produced using ON Semiconductor's trench technology, which is specifically designed to minimize gate charge and low on resistance. This device is suitable for applications with low gate charge driving or low on resistance requirements.



- Low On-Resistance
- 4V drive
- 100% Avalanche Tested
- ESD Diode-Protected Gate
- Pb-Free, Halogen Free and RoHS compliance

## **Typical Applications**

- Reverse Battery Protection
- Load Switch

#### **SPECIFICATIONS**

#### ABSOLUTE MAXIMUM RATING at Ta = 25°C (Note 1, 2)

Parameter		Symbol	Value	Unit
Drain to Source Voltage		VDSS	-100	V
Gate to Source Voltage		VGSS	±20	V
Drain Current (DC)		ID	-11	Α
Drain Current PW ≤ 10µs, duty cycle ≤ 1%		IDP	-44	Α
Power Dissipation		D-	1.0	W
	Tc=25°C	PD	35	W
Junction Temperature		Tj	150	°C
Storage Temperature		Tstg	-55 to +150	°C

Note 1: Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

#### THERMAL RESISTANCE RATINGS

Parameter	Symbol	Value	Unit		
Junction to Case Steady State	$R_{ heta JC}$	3.57	°C/W		
Junction to Ambient (Note 2)	$R_{\theta JA}$	125			

Note 2 : Insertion mounted

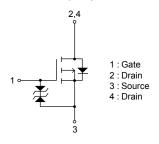


## ON Semiconductor®

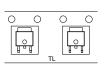
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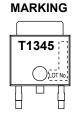
VDSS	RDS(on) Max	ID Max		
-100V	275mΩ@ -10V			
	315mΩ@ –4.5V	-11A		
	330mΩ@ –4V			

# ELECTRICAL CONNECTION P-Channel



#### **PACKING TYPE: TL**









#### **ORDERING INFORMATION**

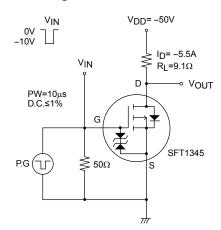
See detailed ordering and shipping information on page 6 of this data sheet.

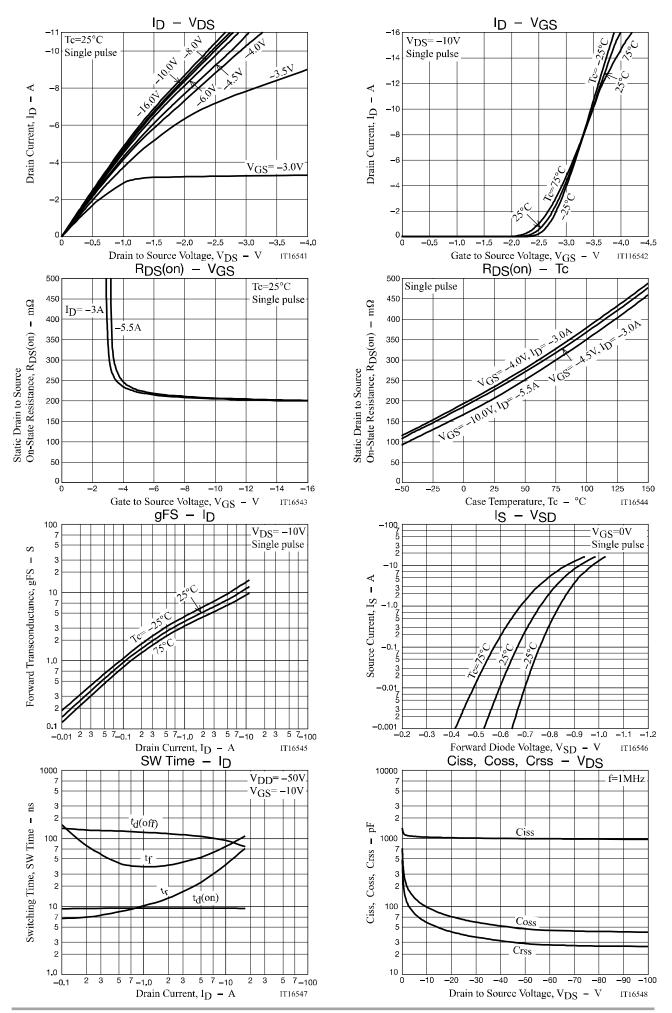
## **ELECTRICAL CHARACTERISTICS** at Ta = 25°C (Note 3)

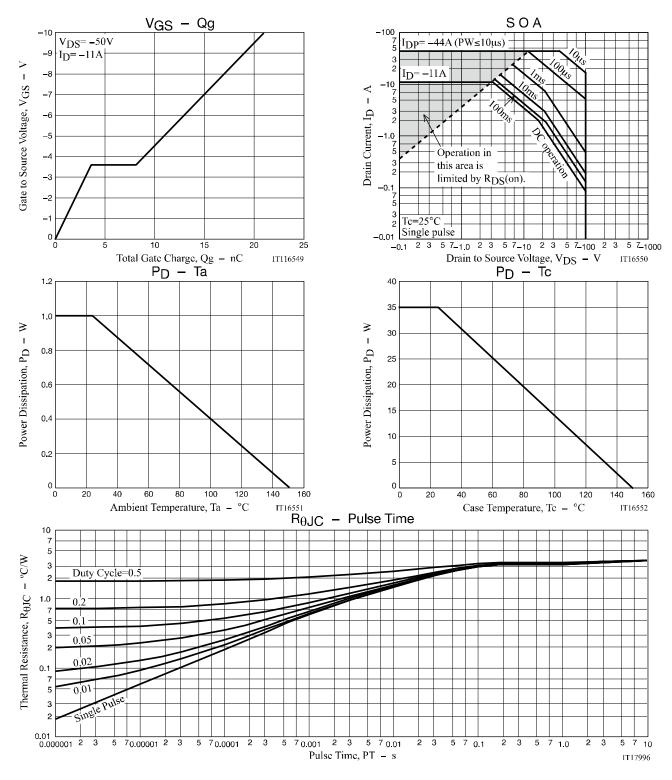
Parameter	Cumbal	Conditions	Value			Unit
Parameter	Symbol	Conditions	min	typ	max	Unit
Drain to Source Breakdown Voltage	V(BR)DSS	ID=-1mA, VGS=0V	-100			V
Zero-Gate Voltage Drain Current	IDSS	V <sub>DS</sub> =-100V, V <sub>GS</sub> =0V			-1	μΑ
Gate to Source Leakage Current	IGSS	V <sub>GS</sub> =±16V, V <sub>DS</sub> =0V			±10	μА
Gate Threshold Voltage	VGS(th)	V <sub>DS</sub> =-10V, I <sub>D</sub> =-1mA	-1.2		-2.6	V
Forward Transconductance	gFS .	V <sub>DS</sub> =-10V, I <sub>D</sub> =-5.5A		8.5		S
	R <sub>DS</sub> (on)1	ID=-5.5A, VGS=-10V		210	275	mΩ
Static Drain to Source On-State Resistance	R <sub>DS</sub> (on)2	I <sub>D</sub> =-3A, V <sub>G</sub> S=-4.5V		225	315	mΩ
Resistance	R <sub>DS</sub> (on)3	I <sub>D</sub> =-3A, V <sub>G</sub> S=-4V		235	330	mΩ
Input Capacitance	Ciss			1020		pF
Output Capacitance	Coss	V <sub>DS</sub> =-20V, f=1MHz		72		pF
Reverse Transfer Capacitance	Crss			43		pF
Turn-ON Delay Time	t <sub>d</sub> (on)			9.5		ns
Rise Time	tr			25		ns
Turn-OFF Delay Time	t <sub>d</sub> (off)	See specified Test Circuit		105		ns
Fall Time	tf			55		ns
Total Gate Charge	Qg			21		nC
Gate to Source Charge	Qgs	V <sub>DS</sub> =-50V, V <sub>GS</sub> =-10V, I <sub>D</sub> =-11A		3.6		nC
Gate to Drain "Miller" Charge	Qgd			4.5		nC
Forward Diode Voltage	V <sub>SD</sub>	I <sub>S</sub> =-11A, V <sub>G</sub> S=0V		-0.93	-1.5	V

Note 3 : Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

# **Switching Time Test Circuit**

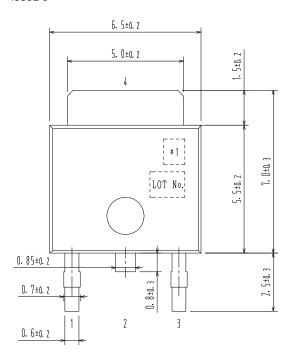


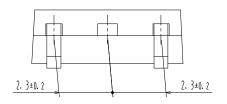




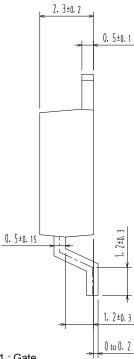
# PACKAGE DIMENSIONS

unit: mm **DPAK / TP-FA** CASE 369AH ISSUE O





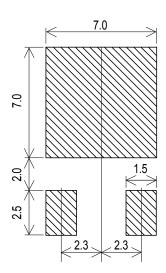
Pin 2 is idle pin with electrical designation only carried.



- 1 : Gate
- 2 : Drain
- 3 : Source
- 4 : Drain

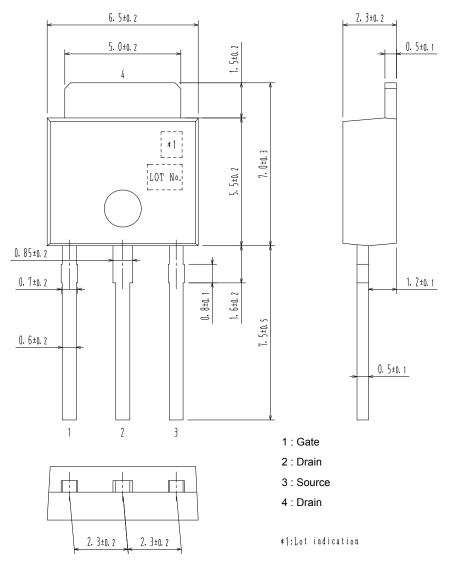
\*1:Lot indication

#### Recommended Soldering Footprint



#### PACKAGE DIMENSIONS

unit: mm IPAK / TP CASE 369AJ ISSUE O



#### **ORDERING INFORMATION**

Device	Marking	Package	Shipping (Qty / Packing)
SFT1345-H	T1345	IPAK / TP (Pb-Free / Halogen Free)	500 / Bag
SFT1345-TL-H	T1345	DPAK / TP-FA (Pb-Free / Halogen Free)	700 / Tape & Reel

<sup>†</sup> For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D. http://www.onsemi.com/pub\_link/Collateral/BRD8011-D.PDF

Note on usage: Since the SFT1345 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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